

## Abstract of the Disclosure

A method for forming a metal interconnect comprises exposing a dielectric layer to an etch chemistry containing nitrogen-containing compound such as  $\text{NH}_3$ ,  $\text{NF}_3$  or  $\text{N}_2\text{O}$ . The nitrogen-containing compound provides selectivity and/or profile control comparable to that provided by  $\text{N}_2$ , while avoiding poisoning of photoresist by embedded  $\text{N}_2$ .